### SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

#### **Features**

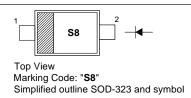
- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

# **Applications**

• High speed switching

#### **PINNING**

PIN	DESCRIPTION
1	Cathode
2	Anode



# Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	40	V
Reverse Voltage	$V_R$	30	V
Mean Rectifying Current	Io	30	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I <sub>FSM</sub>	200	mA
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature Range	T <sub>s</sub>	- 40 to + 125	°C

## Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at I <sub>F</sub> = 1 mA	V <sub>F</sub>	-	0.37	V
Reverse Current at V <sub>R</sub> = 30 V	I <sub>R</sub>	-	0.5	μΑ
Capacitance Between Terminals at $V_R = 1 \text{ V}$ , $f = 1 \text{ MHz}$	Ст	2	-	pF

Note: ESD sensitive product handling required.

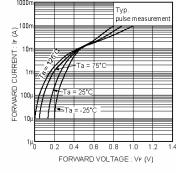


Fig. 1 Forward characteristics

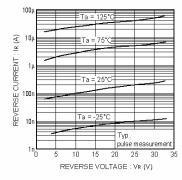


Fig. 2 Reverse characteristics

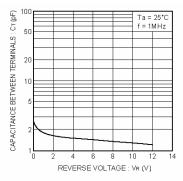


Fig. 3 Capacitance between terminals characteristics



# SEMTECH ELECTRONICS LTD.

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## **PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

**SOD-323** 

